

LH52256C/CH

CMOS 256K (32K × 8) Static RAM

FEATURES

- 32,768 × 8 bit organization
- Access time: 70 ns (MAX.)
- Supply current:
 - Operating: 45 mA (MAX.)
 - 10 mA (MAX.) (t_{RC} , $t_{WC} = 1 \mu s$)
 - Standby: 40 μA (MAX.)
- Data retention current: 1.0 μA (MAX.)
 - ($V_{CCDR} = 3 V$, $T_A = 25^\circ C$)
- Wide operating voltage range:
 - 4.5 V $\pm$ 5.5 V
- Operating temperature:
 - Commerical temperature 0°C to +70°C
 - Industrial temperature -40° to +85°C
- Fully-static operation
- Three-state outputs
- Not designed or rated as radiation hardened
- Package:
 - 28-pin, 600-mil DIP
 - 28-pin, 450-mil SOP
 - 28-pin, 300-mil SK-DIP
 - 28-pin, 8 × 3 mm² TSOP (Type I)
- N-type bulk silicon

DESCRIPTION

The LH52256C is a Static RAM organized as 32,768 × 8 bits which provides low-power standby mode. It is fabricated using silicon-gate CMOS process technology.

PIN CONNECTIONS

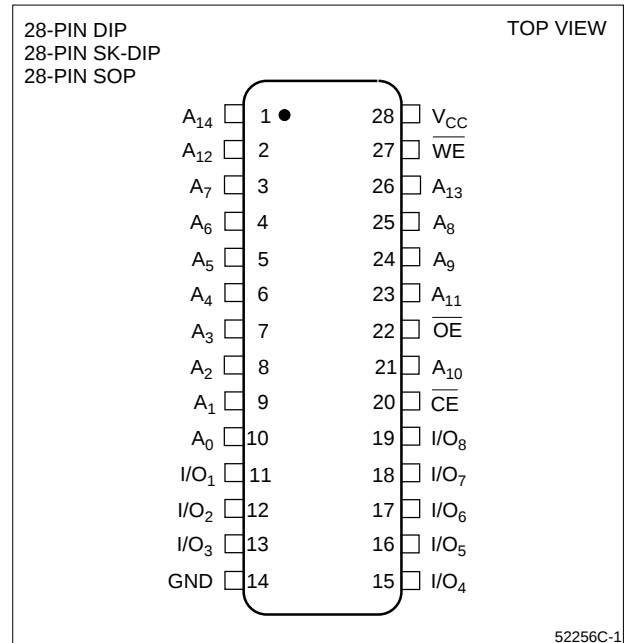


Figure 1. Pin Connections

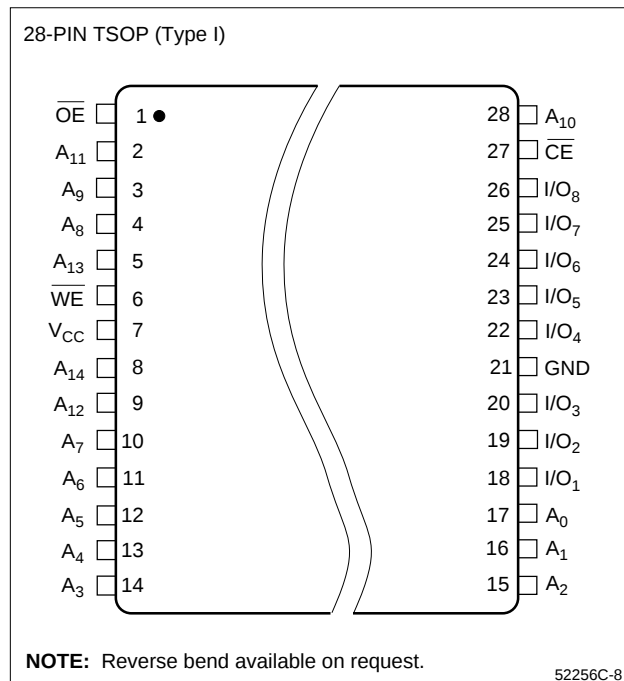


Figure 2. TSOP (Type I) Pin Connections

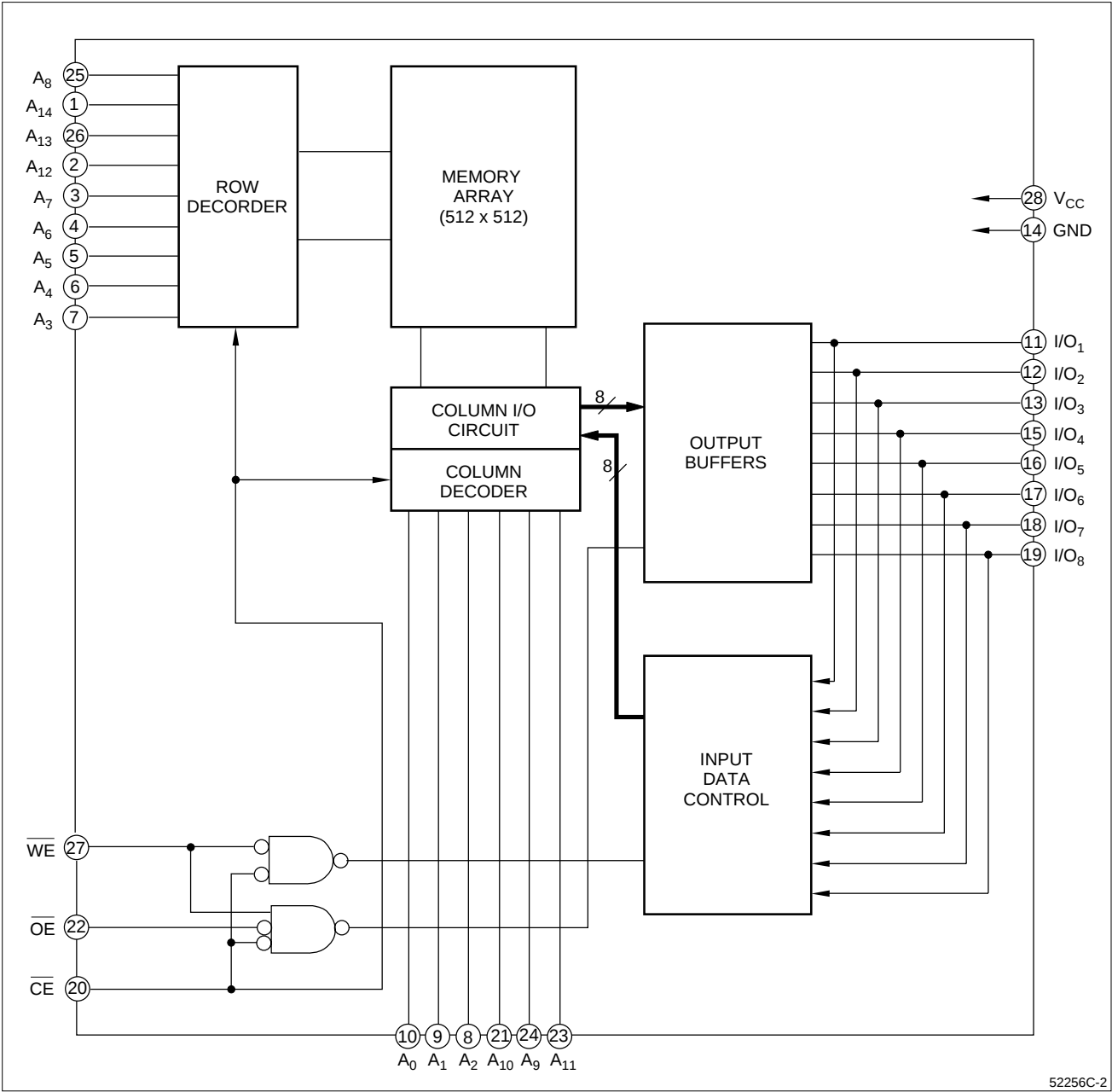


Figure 3. LH52256C Block Diagram

PIN DESCRIPTION

SIGNAL	PIN NAME
A ₀ - A ₁₄	Address inputs
CE	Chip enable
WE	Write enable
OE	Output enable

SIGNAL	PIN NAME
I/O ₁ - I/O ₈	Data inputs and outputs
V _{CC}	Power supply
GND	Ground

TRUTH TABLE

$\overline{\text{CE}}$	$\overline{\text{WE}}$	$\overline{\text{OE}}$	MODE	I/O ₁ - I/O ₈	SUPPLY CURRENT	NOTE
H	X	X	Standby	High impedance	Standby (I _{SB})	1
L	H	L	Read	Data output	Active (I _{CC})	1
L	H	H	Output disable	High impedance	Active (I _{CC})	1
L	L	X	Write	Data input	Active (I _{CC})	1

NOTE:

1. X = Don't care, L = Low, H = High

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	RATING	UNIT	NOTE
Supply voltage	V _{CC}	−0.5 to +7.0	V	1
Input voltage	V _{IN}	−0.5 to V _{CC} + 0.5	V	1, 2
Operating temperature	T _{OPR}	0 to +70	°C	—
Storage temperature	T _{STG}	−65 to +150	°C	—

NOTES:

1. The maximum applicable voltage on any pin with respect to GND.
2. Undershoot of -3.0 V is allowed width of pulse below 50 ns.

RECOMMENDED DC OPERATING CONDITIONS (T_A = 0°C to +70°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	NOTE
Supply voltage	V _{CC}	4.5	5.0	5.5	V	—
Input voltage	V _{IH}	2.2	—	V _{CC} + 0.5	V	—
	V _{IL}	−0.5	—	0.8	V	1

NOTE:

1. Undershoot of -3.0 V is allowed width of pulse below 50 ns.

DC ELECTRICAL CHARACTERISTICS ($T_A = 0^\circ\text{C}$ to $+70^\circ\text{C}$, $V_{CC} = 4.5\text{ V}$ to 5.5 V)

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Input leakage current	I_{LI}	$V_{IN} = 0\text{ V to }V_{CC}$	-1.0	—	1.0	μA
Output leakage current	I_{LO}	$\overline{CE} = V_{IH}$ or $\overline{OE} = V_{IH}$ $V_{IO} = 0\text{ V to }V_{CC}$	-1.0	—	1.0	μA
Operating supply current	I_{CC}	Minimum cycle, $V_{IN} = V_{IL}$ or V_{IH} $I_{IO} = 0\text{ mA}$, $\overline{CE} = V_{IL}$	—	25	45.0	mA
	I_{CC1}	$t_{RC}, t_{WC} = 1\text{ }\mu\text{s}$, $V_{IN} = V_{IL}$ or V_{IH} , $I_{IO} = 0\text{ mA}$, $\overline{CE} = V_{IL}$	—	—	10.0	
Standby current	I_{SB}	$\overline{CE} \geq V_{CC} - 0.2\text{ V}$	—	0.6	40.0	μA
	I_{SB1}	$\overline{CE} = V_{IH}$	—	—	3.0	mA
Output voltage	V_{OL}	$I_{OL} = 2.1\text{ mA}$	—	—	0.4	V
	V_{OH}	$I_{OH} = -1.0\text{ mA}$	2.4	—	—	

NOTE:Typical values at $V_{CC} = 5.0\text{ V}$, $T_A = 25^\circ\text{C}$ **AC ELECTRICAL CHARACTERISTICS****AC Test Conditions**

PARAMETER	MODE	NOTE
Input pulse level	0.6 V to 2.4 V	—
Input rise and fall time	10 ns	—
Input and output timing Ref. level	1.5 V	—
Output load	1 TTL + C_L (100 pF)	1

NOTE:

1. Including scope and jig capacitance.

READ CYCLE ($T_A = 0^\circ\text{C}$ to $+70^\circ\text{C}$, $V_{CC} = 4.5\text{ V}$ to 5.5 V)

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	NOTE
Read cycle time	t_{RC}	70	—	ns	—
Address access time	t_{AA}	—	70	ns	—
$\overline{CE}$ access time	t_{ACE}	—	70	ns	—
Output enable to output valid	t_{OE}	—	35	ns	—
Output hold from address change	t_{OH}	10	—	ns	—
$\overline{CE}$ Low to output active	t_{LZ}	10	—	ns	1
$\overline{OE}$ Low to output active	t_{OLZ}	5	—	ns	1
$\overline{CE}$ High to output in High impedance	t_{HZ}	0	30	ns	1
$\overline{OE}$ High to output in High impedance	t_{OHZ}	0	30	ns	1

NOTES:

1. Active output to high-impedance and high-impedance to output active tests specified for a $\pm 200\text{ mV}$ transition from steady state levels into the test load.

WRITE CYCLE ($T_A = 0^\circ\text{C}$ to $+70^\circ\text{C}$, $V_{CC} = 4.5\text{ V}$ to 5.5 V)

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	NOTE
Write cycle time	t_{WC}	70	—	ns	—
CE Low to end of write	t_{CW}	45	—	ns	—
Address valid to end of write	t_{AW}	45	—	ns	—
Address setup time	t_{AS}	0	—	ns	—
Write pulse width	t_{WP}	35	—	ns	—
Write recovery time	t_{WR}	0	—	ns	—
Input data setup time	t_{DW}	30	—	ns	—
Input data hold time	t_{DH}	0	—	ns	—
$\overline{WE}$ High to output active	t_{OW}	5	—	ns	1
$\overline{WE}$ Low to output in High impedance	t_{WZ}	0	30	ns	1
OE High to output in High impedance	t_{OHZ}	0	30	ns	1

NOTE:

- Active output to high-impedance and high-impedance to output active tests specified for a $\pm 200\text{ mV}$ transition from steady state levels into the test load.

CAPACITANCE ($T_A = 25^\circ\text{C}$, $f = 1\text{ MHz}$)

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNIT	NOTE
Input capacitance	C_{IN}	$V_{IN} = 0\text{ V}$	—	—	7	pF	1
I/O capacitance	$C_{I/O}$	$V_{I/O} = 0\text{ V}$	—	—	10	pF	1

NOTE:

- This parameter is sampled and not production tested.

DATA RETENTION CHARACTERISTICS ($T_A = 0^\circ\text{C}$ to $+70^\circ\text{C}$)

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNIT	NOTE
Data retention supply voltage	V_{CCDR}	$\overline{CE} \geq V_{CCDR} - 0.2\text{ V}$	2.0	—	5.5	V	—
Data retention supply current	I_{CCDR}	$V_{CCDR} = 3.0\text{ V}$	—	0.3	1.0	μA	—
		$T_A = 25^\circ\text{C}$		—	3.0		—
		$T_A = 40^\circ\text{C}$	—	—	—	—	—
		$\overline{CE} \geq V_{CCDR} - 0.2\text{ V}$			15		
Chip enable setup time	t_{CDR}	—	0	—	—	ns	—
Chip enable hold time	t_R	—	t_{RC}	—	—	ns	1

NOTE:

- t_{RC} = Read cycle time.
- Typical values at $T_A = 25^\circ\text{C}$

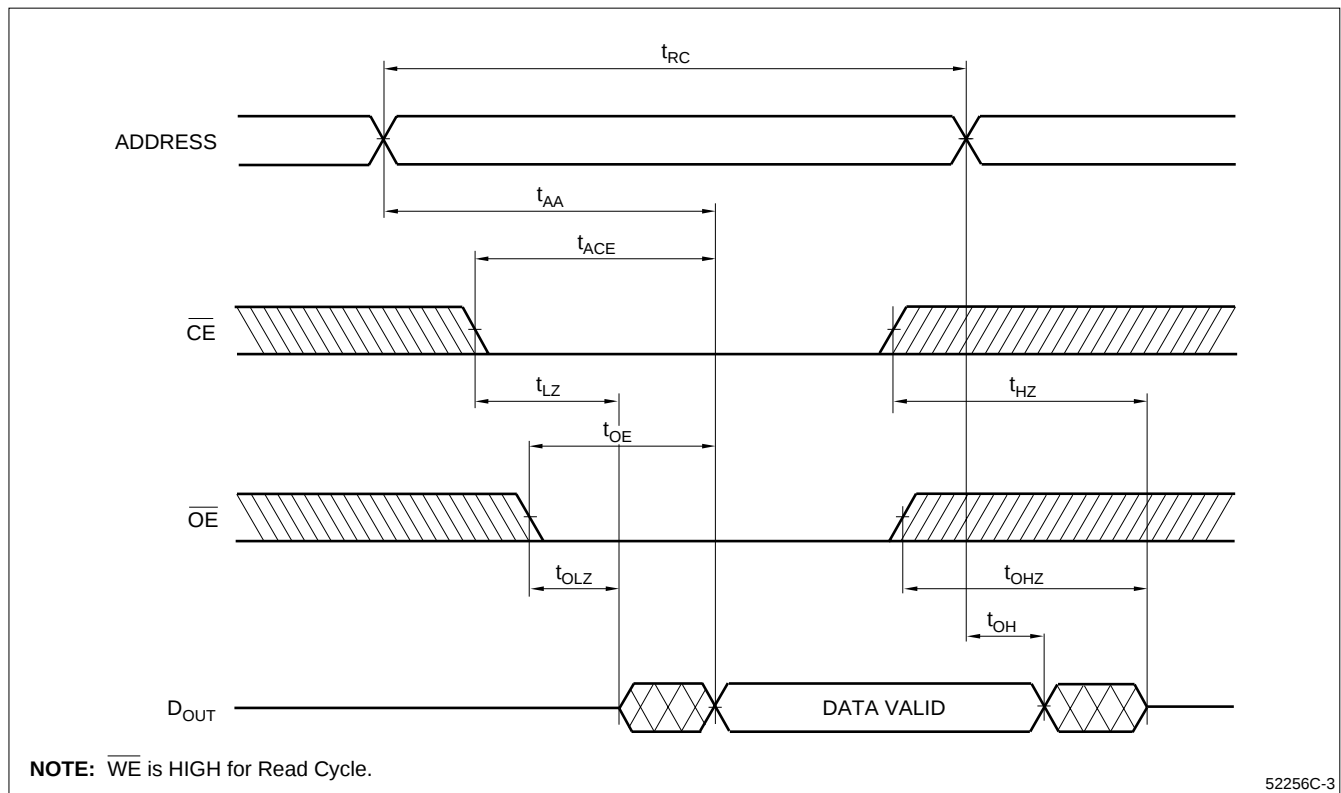
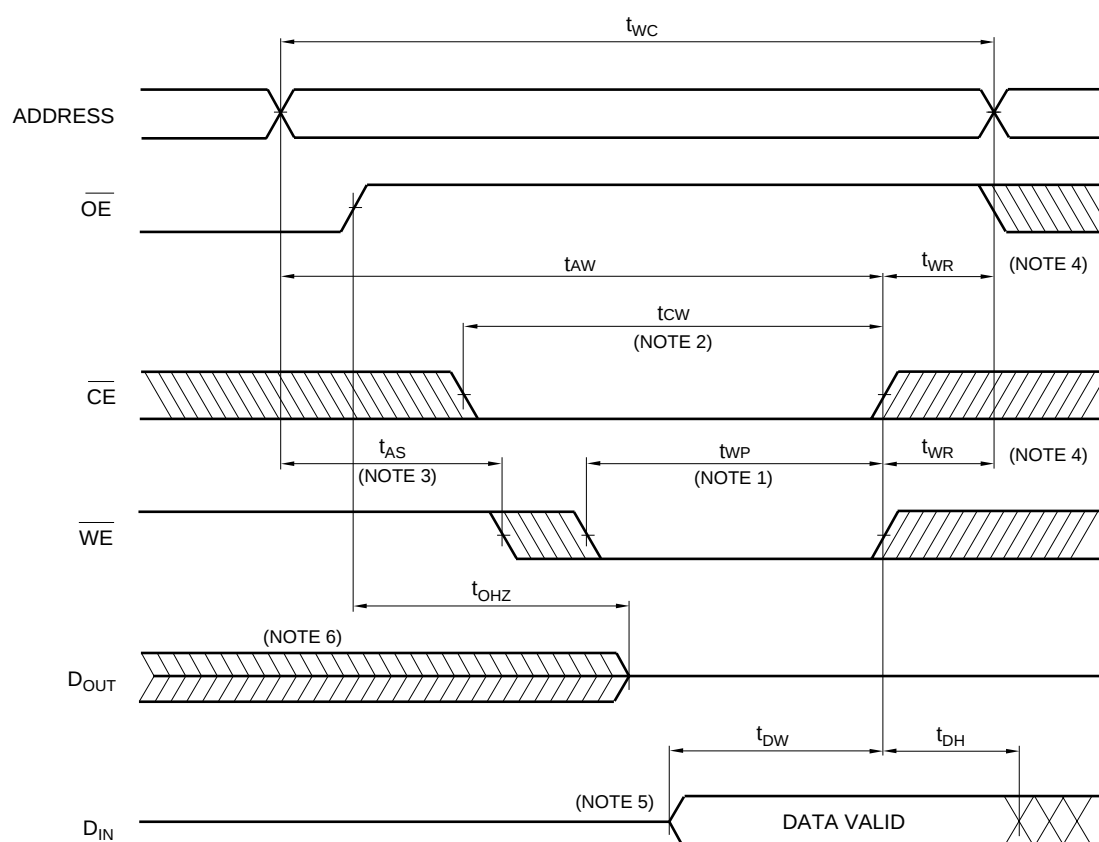


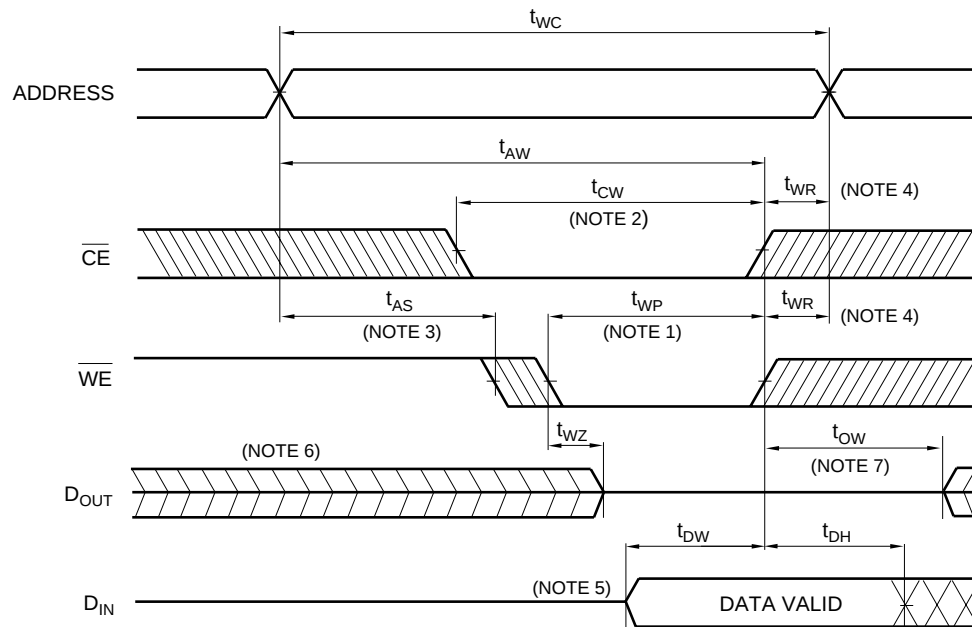
Figure 4. Read Cycle

**NOTES:**

1. A write occurs during the overlap of a LOW $\overline{CE}$ and a LOW $\overline{WE}$. A write begins at the latest transition among $\overline{CE}$ going LOW, and $\overline{WE}$ going LOW. A write ends at the earliest transition among $\overline{CE}$ going HIGH, and $\overline{WE}$ going HIGH. t_{WP} is measured from the beginning of write to the end of write.
2. t_{CW} is measured from the later of $\overline{CE}$ going LOW to the end of write.
3. t_{AS} is measured from the address valid to the beginning of write.
4. t_{WR} is measured from the end of write to the address change.
5. During this period, I/O pins are in the output state, therefore the input signals of opposite phase to the outputs must not be applied.
6. If $\overline{CE}$ goes LOW simultaneously with $\overline{WE}$ going LOW or after $\overline{WE}$ going LOW, the outputs remain in high impedance state.
7. If $\overline{CE}$ goes HIGH simultaneously with $\overline{WE}$ going HIGH or before $\overline{WE}$ going HIGH, the outputs remain in high impedance state.

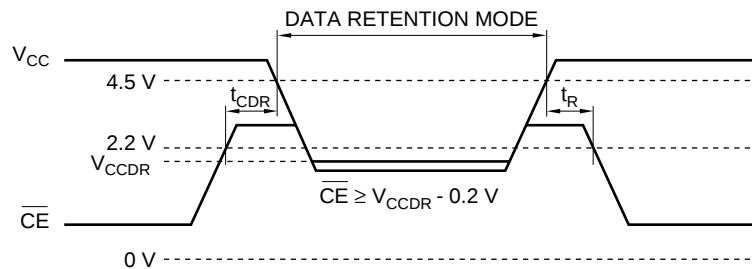
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Figure 5. Write Cycle (OE Controlled)

**NOTES:**

1. A write occurs during the overlap of a LOW $\overline{CE}$, and a LOW $\overline{WE}$.
A write begins at the latest transition among $\overline{CE}$ going LOW, and $\overline{WE}$ going LOW. A write ends at the earliest transition among $\overline{CE}$ going HIGH, and $\overline{WE}$ going HIGH. t_{WP} is measured from the beginning of write to the end of write.
2. t_{CW} is measured from the later of $\overline{CE}$ going LOW to the end of write.
3. t_{AS} is measured from the address valid to the beginning of write.
4. t_{WR} is measured from the end of write to the address change.
5. During this period, I/O pins are in the output state, therefore the input signals of opposite phase to the outputs must not be applied.
6. If $\overline{CE}$ goes LOW simultaneously with $\overline{WE}$ going LOW or after $\overline{WE}$ going LOW, the outputs remain in high impedance state.
7. If $\overline{CE}$ goes HIGH simultaneously with $\overline{WE}$ going HIGH or before $\overline{WE}$ going HIGH, the outputs remain in high impedance state.

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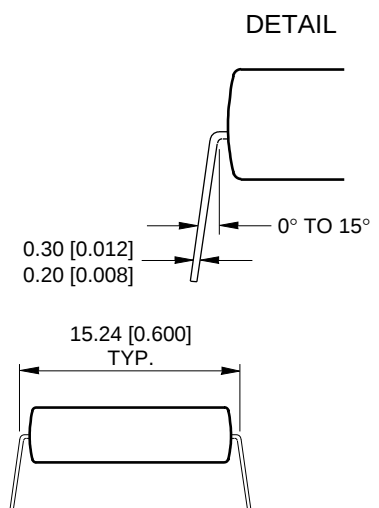
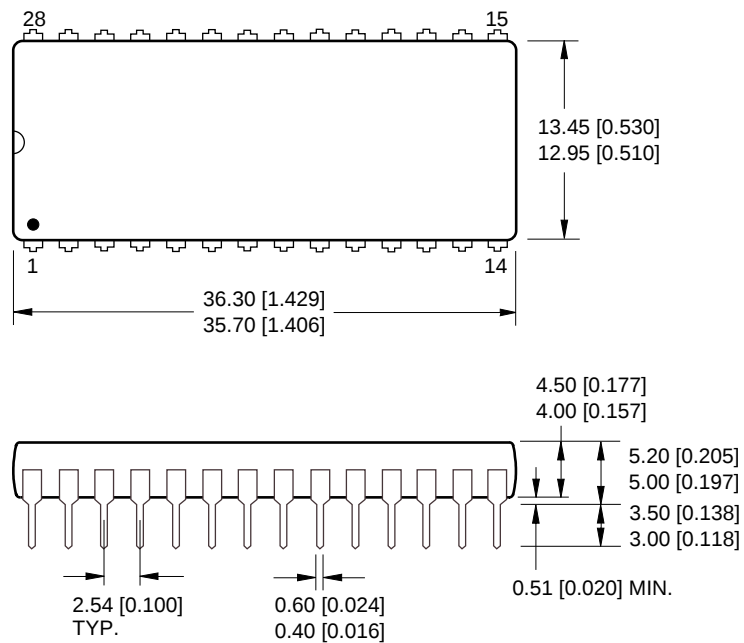
Figure 6. Write Cycle ($\overline{OE}$ Low Fixed) **$\overline{CE}$ CONTROL**

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**Data Retention Timing Chart
CE Controlled**

PACKAGE DIAGRAMS

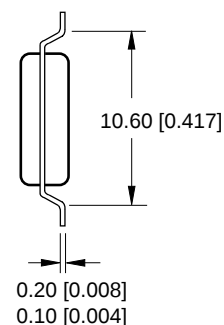
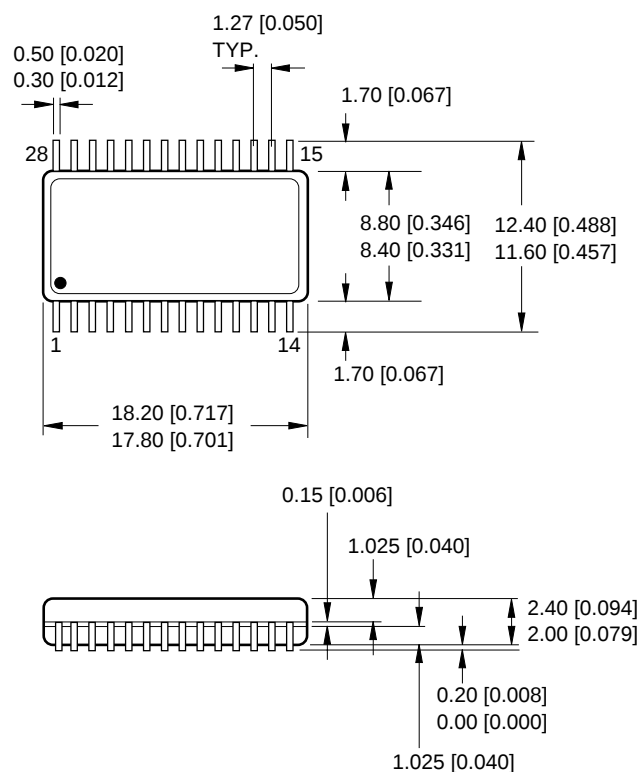
28DIP (DIP028-P-0600)



DIMENSIONS IN MM [INCHES] MAXIMUM LIMIT
MINIMUM LIMIT

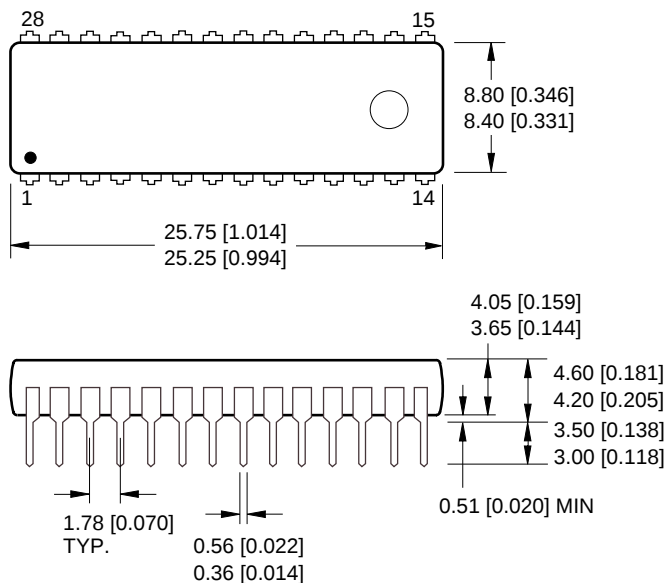
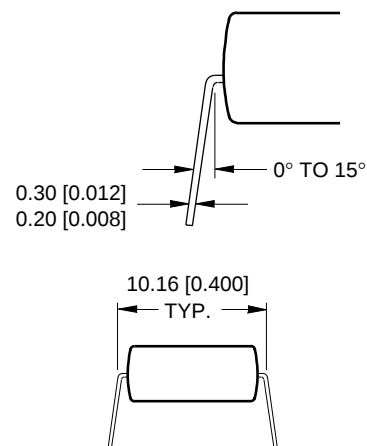
28DIP-2

28SOP (SOP028-P-0450)



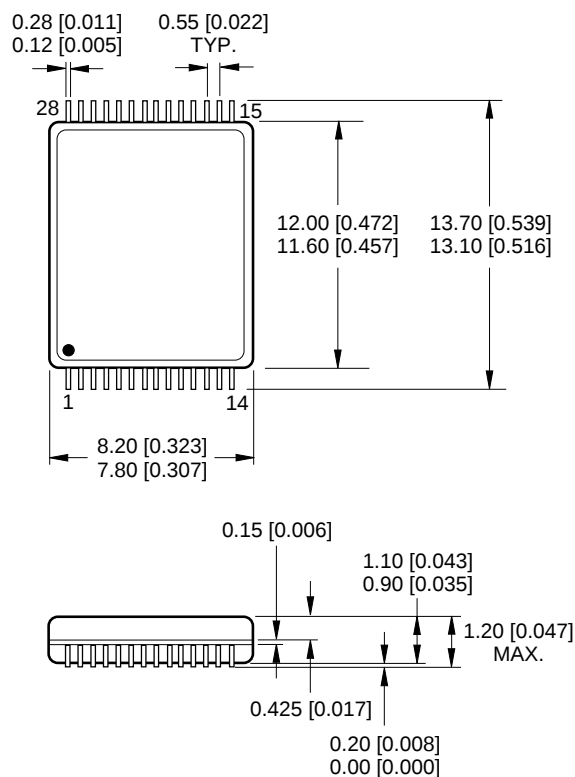
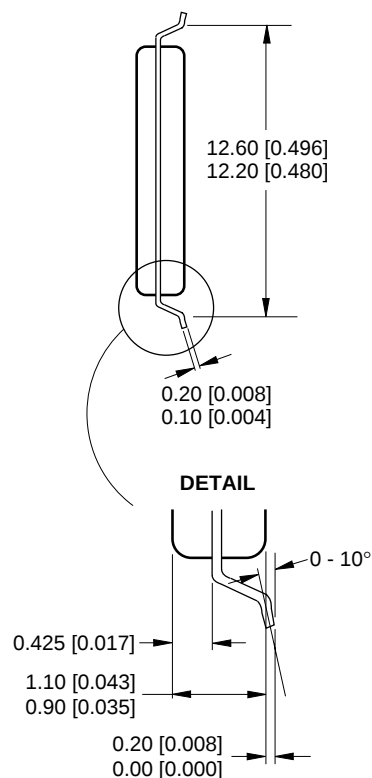
DIMENSIONS IN MM [INCHES] MAXIMUM LIMIT
MINIMUM LIMIT

28SOP

28SDIP (SDIP28-P-400)**DETAIL**

DIMENSIONS IN MM [INCHES] MAXIMUM LIMIT
MINIMUM LIMIT

28SDIP

28TSOP (TSOP028-P-0813)**DETAIL**

DIMENSIONS IN MM [INCHES] MAXIMUM LIMIT
MINIMUM LIMIT

28TSOP

ORDERING INFORMATION

LH52256C

Device Type

X

Operating Temp

X

Package

- ##

Speed

LL

Power

Low-Low-power standby

70 Access Time (ns)

Blank 28-pin, 600-mil DIP (DIP028-P-0600)

D 28-pin, 300-mil SK-DIP (DIP028-P-0300)

N 28-pin, 450-mil SOP (SOP028-P-0450)

T 28-pin, 8 x 13 mm² TSOP (Type I) (TSOP028-P-0813)

Blank 0° to +70°C

H -4° to +85°C

CMOS 32K x 8 Static RAM

Example: LH52256C-70LL (CMOS 32K x 8 Static RAM, Low-Low-power standby, 70 ns, 28-pin, 600-mil DIP)

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